

FIG. 1

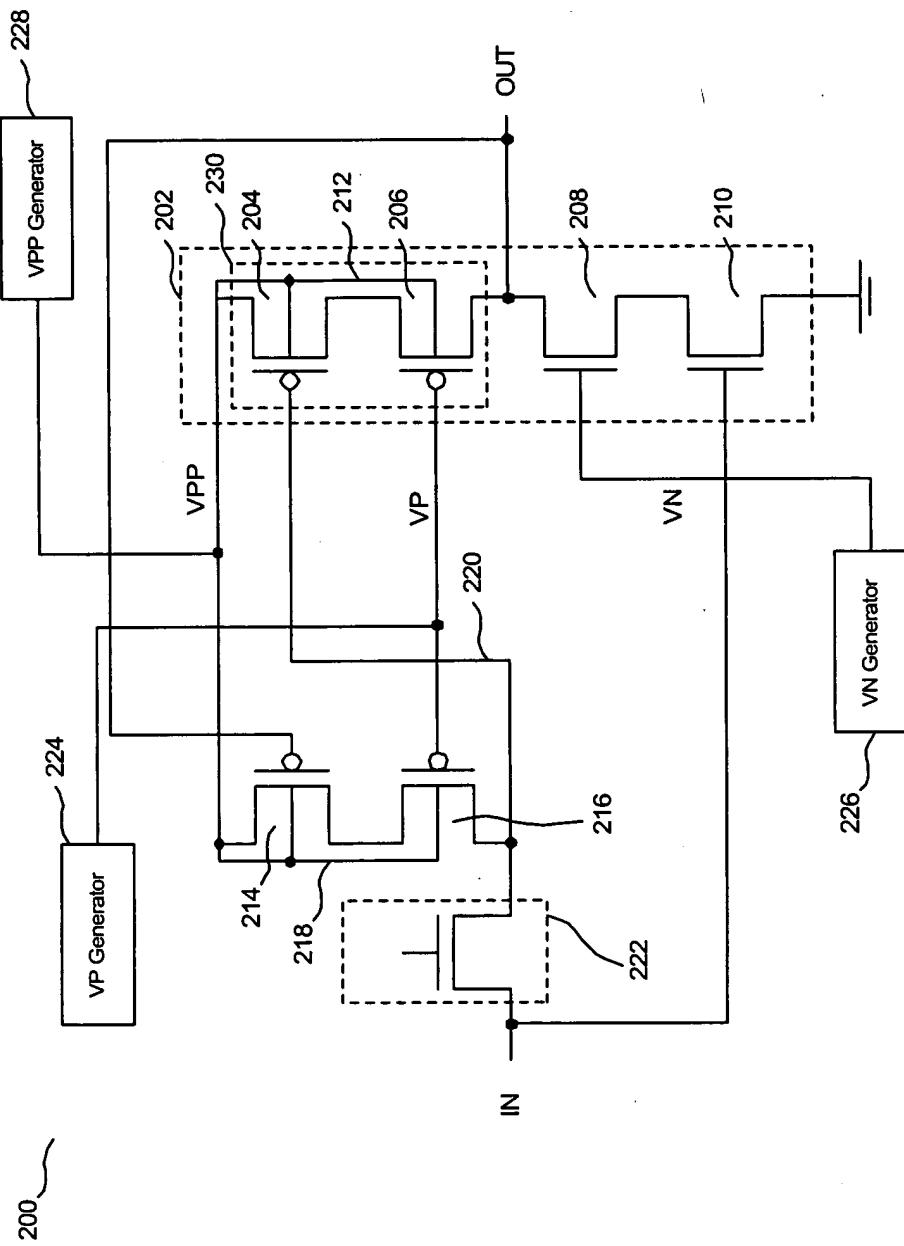


FIG. 2A

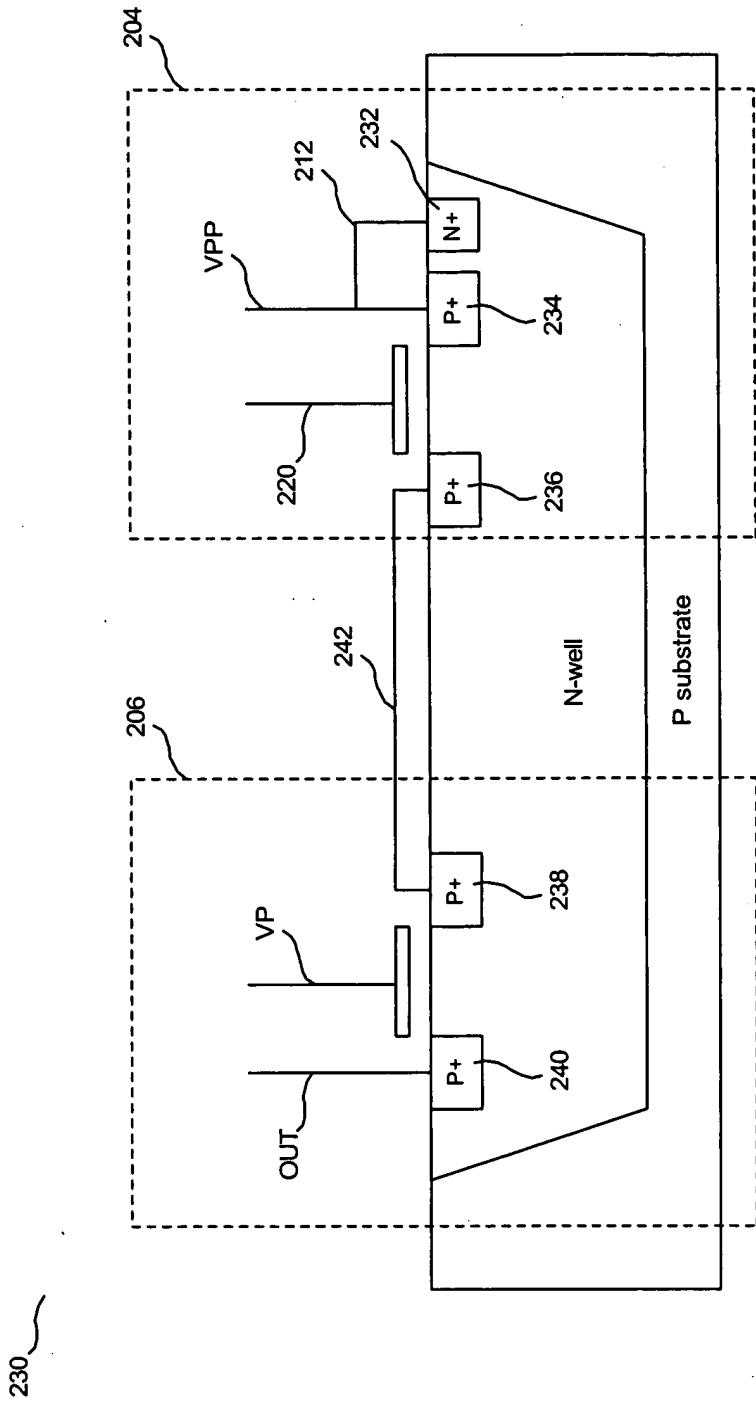


FIG. 2B

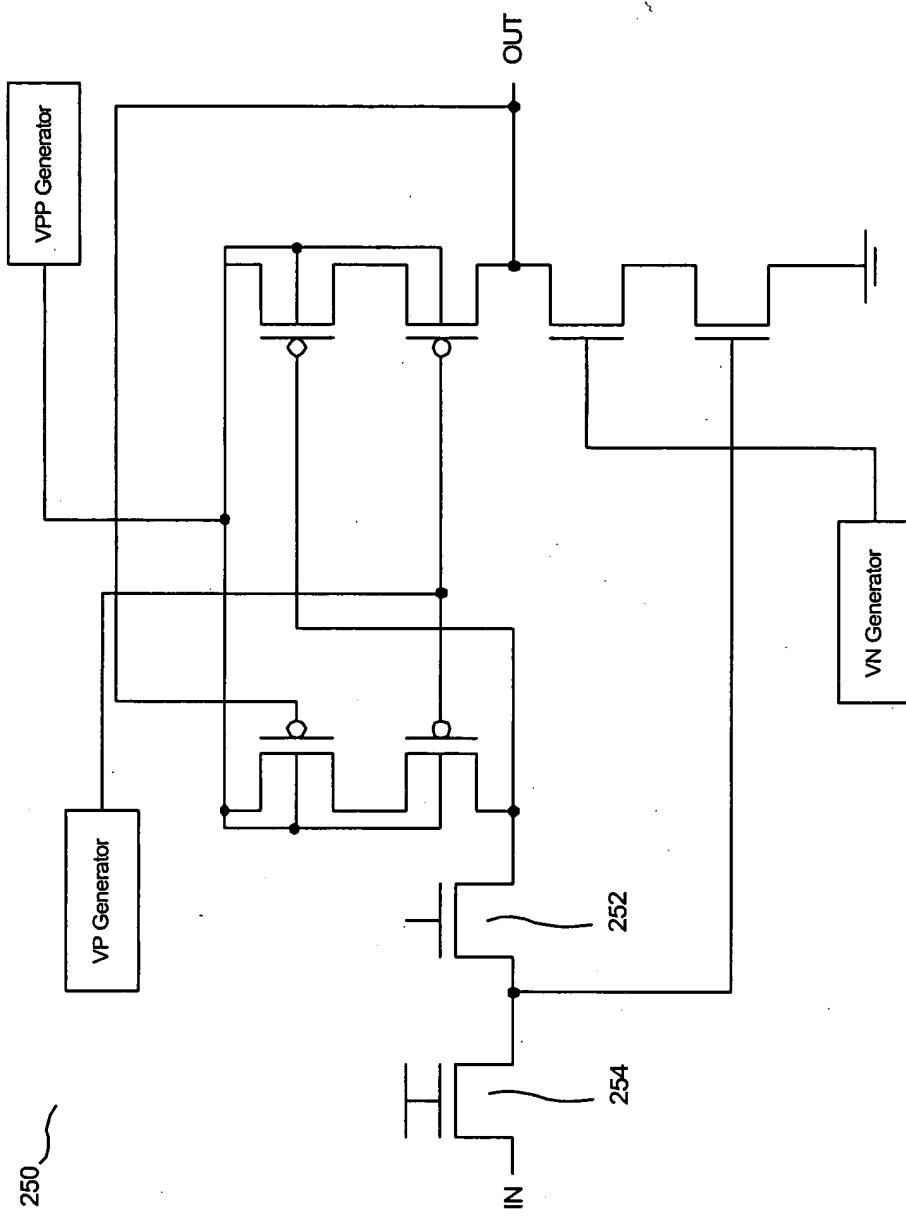


FIG. 2C

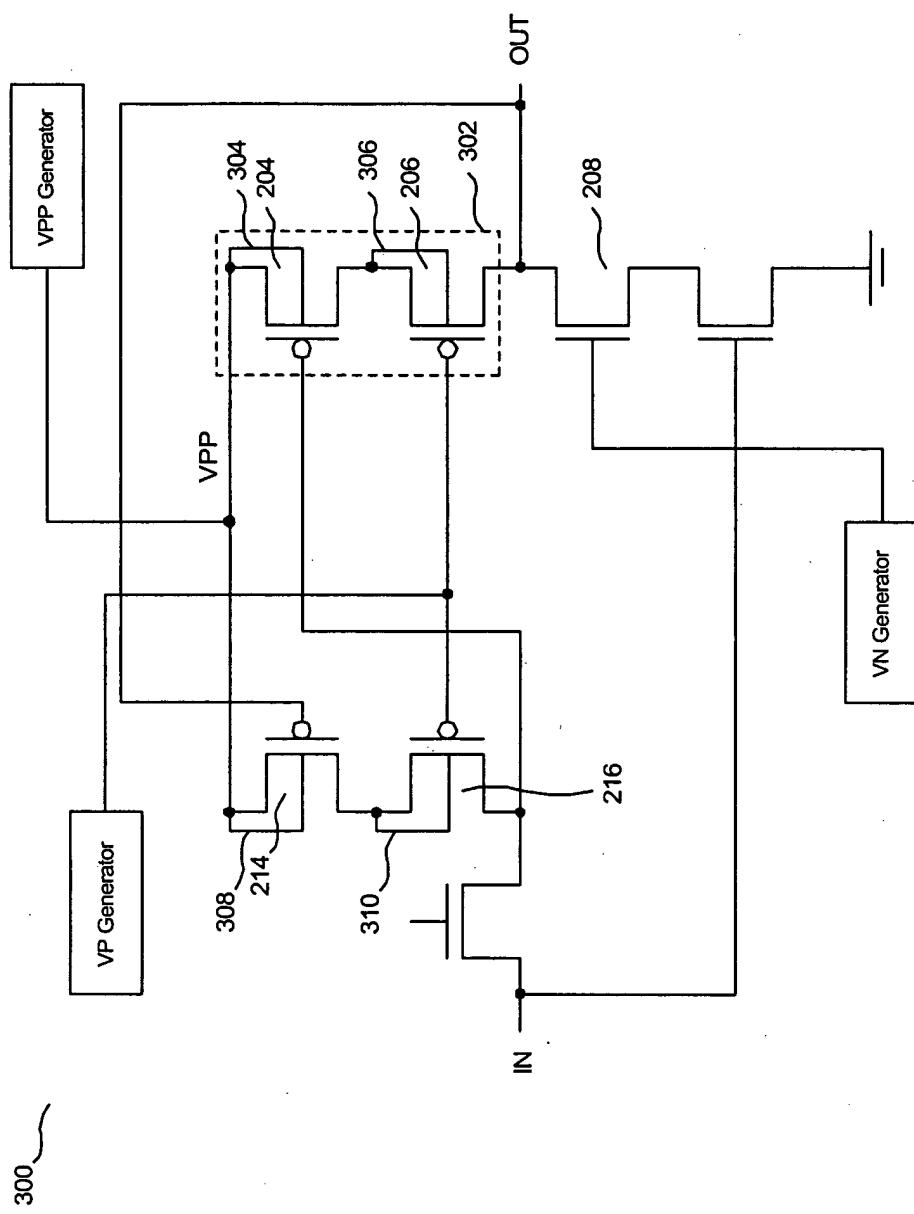


FIG. 3A

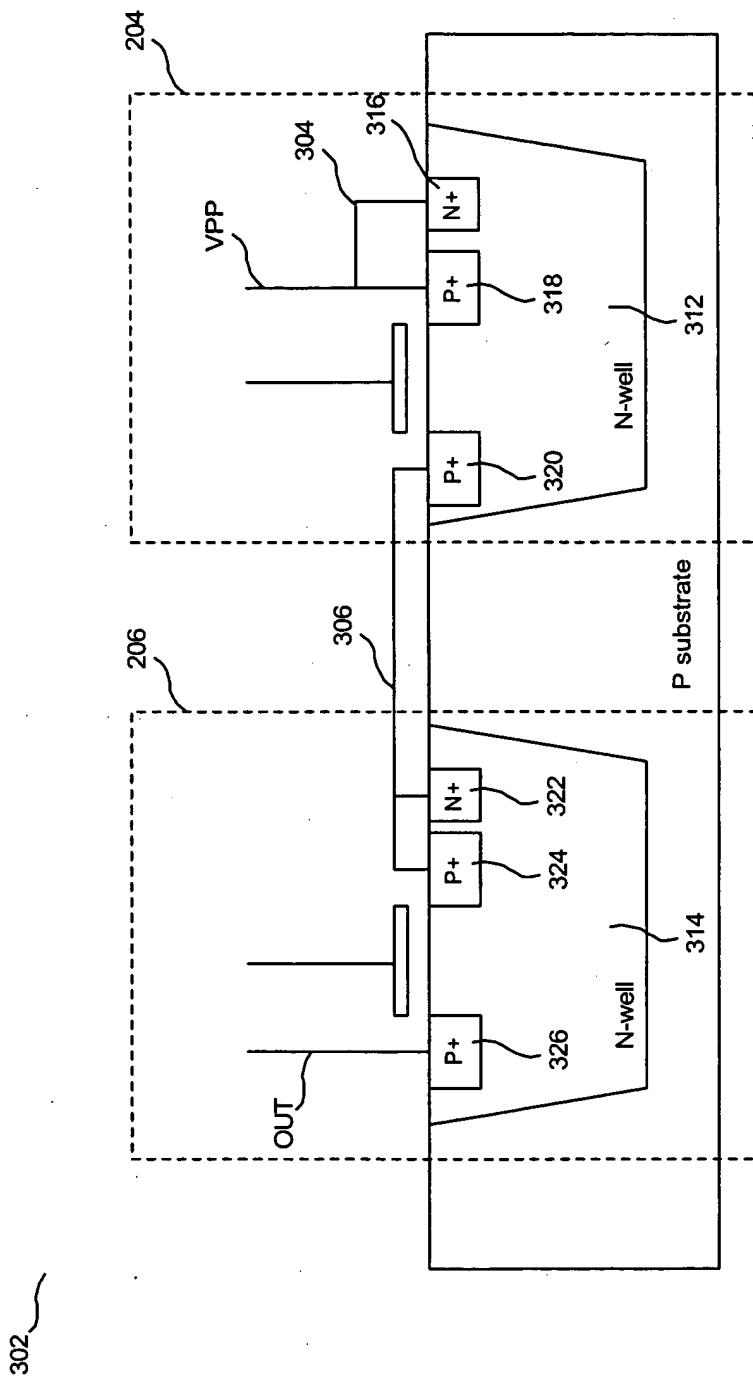


FIG. 3B

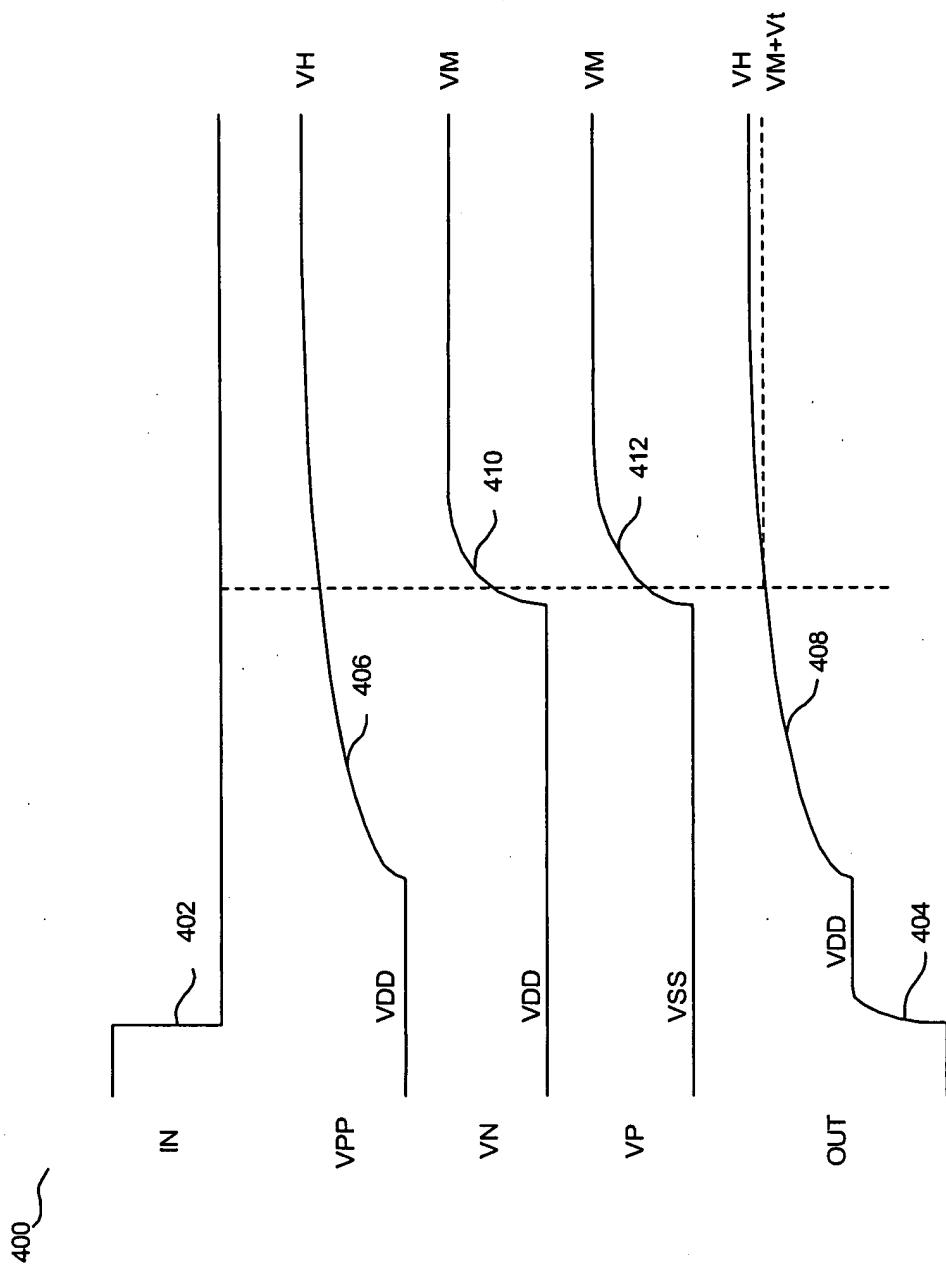


FIG. 4

500

Stress Voltage	Switch circuit 100	Switch circuit 300
drain to source (punch through)	< (VH - VDD + V _{tn}) for nMOS > -(VH - VDD + V _{tp}) for pMOS	< (VH - VM + V _{tn}) for nMOS > -(VH - VM + V _{tp}) for pMOS
drain to gate (gated breakdown)	VH - VDD for nMOS -(VH - VDD) for pMOS	VM - VM for nMOS -(VH - VM) for pMOS

FIG. 5A

502

Stress Voltage	Switch circuit 100	Switch circuit 300
drain to source (punch through)	< 11.7V for nMOS > -11.7V for pMOS	< 7.0V for nMOS > -7.0V for pMOS
drain to gate (gated breakdown)	11.2V for nMOS -11.2V for pMOS	6.5V for nMOS -6.5V for pMOS

FIG. 5B

U.S. Patent Appln : HIGH VOLTAGE CMOS SWITCH WITH REDUCED HIGH VOLTAGE JUNCTION STRESSES

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FIG. 6B

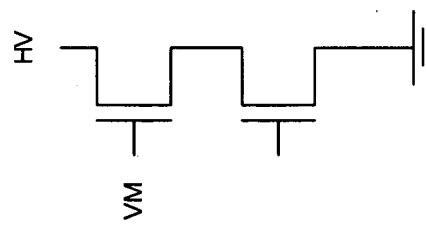


FIG. 6A

